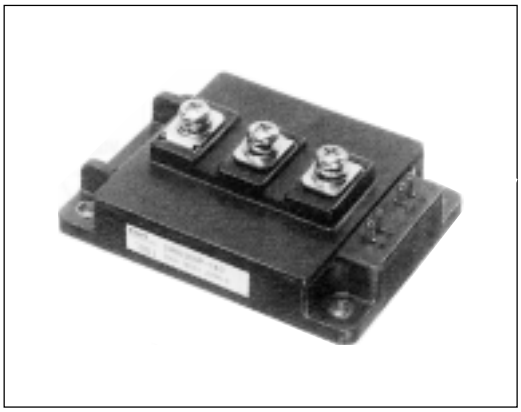
2MBI600NT-060

IGBT Module

600V / 600A 2 in one-package



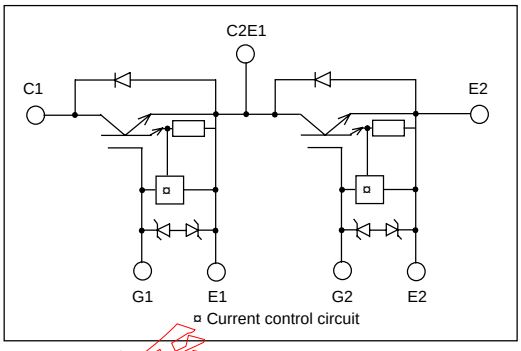
■ Features

· VCE(sat) classified for easy parallel connection
· High speed switching
· Voltage drive
· Low inductance module structure

■ Applications

· Inverter for Motor drive
· AC and DC Servo drive amplifier
· Uninterruptible power supply
· Industrial machines, such as Welding machines

■ Equivalent Circuit Schematic



■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item		Symbol	Rating	Unit
Collector-Emitter voltage		V_{CES}	600	V
Gate-Emitter voltage		V_{GES}	±20	V
Collector current	Continuous	I_C	600	A
	1ms	I_C pulse	1200	A
		-I_C	600	A
	1ms	-I_C pulse	1200	A
Max. power dissipation		P_C	2500	W
Operating temperature		T_j	+150	°C
Storage temperature		T_{stg}	-40 to +125	°C
Isolation voltage		V_{is}	AC 2500 (1min.)	V
Screw torque		Mounting *1	3.5	N·m
		Terminals *2	4.5	N·m

*1 : Recommendable value : 2.5 to 3.5N·m (M5) or (M6)
*2 : Recommendable value : 3.5 to 4.5N·m (M6)

使用不推荐 Not recommend for new design.

● Electrical characteristics (at Tj=25°C unless otherwise specified)

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Zero gate voltage collector current	I_{CES}	–	–	4.0	V_{GE}=0V, V_{CE}=600V	mA
Gate-Emitter leakage current	I_{GES}	–	–	60	V_{CE}=0V, V_{GE}=±20V	µA
Gate-Emitter threshold voltage	$V_{GE(th)}$	4.5	–	7.5	V_{CE}=20V, I_C=600mA	V
Colloctor-Emitter saturation voltage	$V_{CE(sat)}$	–	–	2.9	V_{GE}=15V, I_C=600A	V
Input capacitance	C_{ies}	–	39600	–	V_{GE}=0V	pF
Output capacitance	C_{oes}	–	8800	–	V_{CE}=10V	
Reverse transfer capacitance	C_{res}	–	2670	–	f=1MHz	
Turn-on time	t_{on}	–	0.6	1.2	V_{CC}=300V	µs
	t_r	–	0.2	0.6	I_C=600A	
Turn-off time	t_{off}	–	0.6	1.0	V_{GE}=±15V	
	t_f	–	0.2	0.35	R_G=2.7ohm	
Diode forward on voltage	V_F	–	–	3.1	I_F=600A, V_{GE}=0V	V
Reverse recovery time	t_{rr}	–	–	0.3	I_F=600A	µs

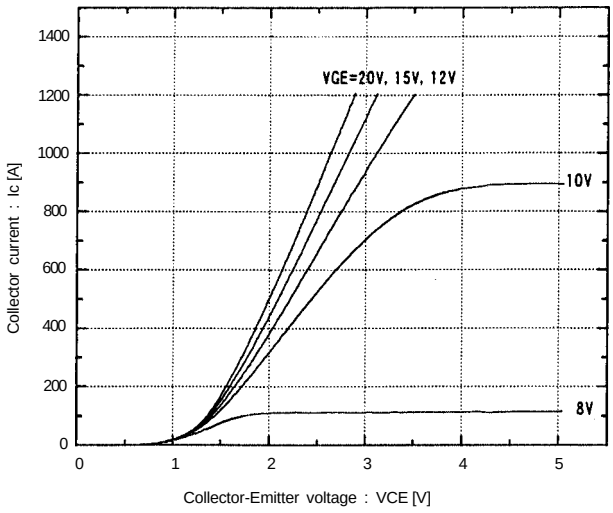
● Thermal resistance characteristics

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Thermal resistance	Rth(j-c)	–	–	0.05	IGBT	°C/W
	Rth(j-c)	–	–	0.1	Diode	°C/W
	Rth(c-f)*	–	0.0167	–	the base to cooling fin	°C/W

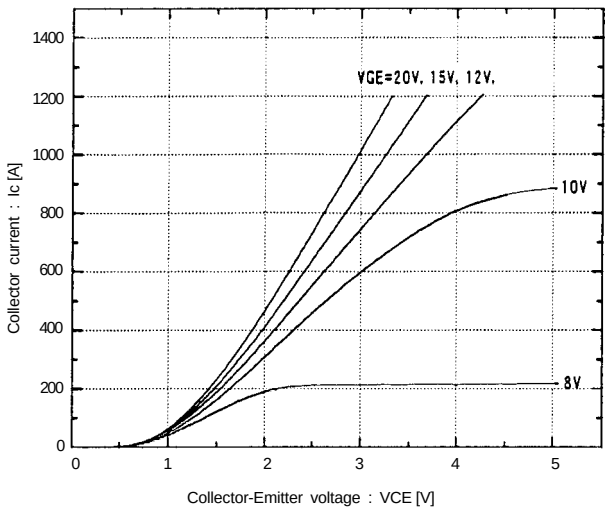
* : This is the value which is defined mounting on the additional cooling fin with thermal compound

■ Characteristics (Representative)

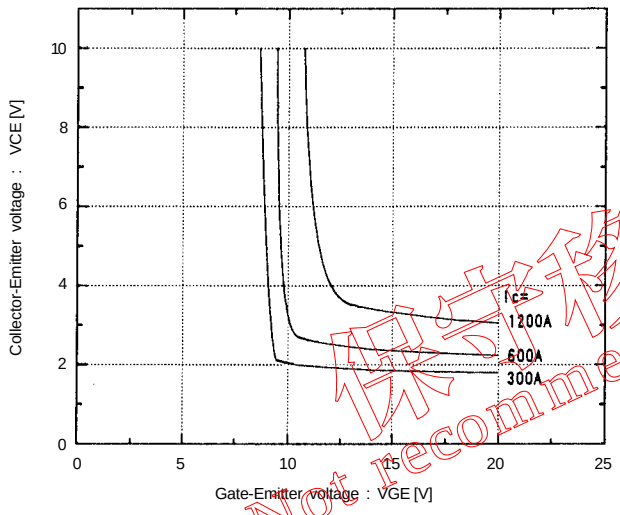
Collector current vs. Collector-Emitter voltage
Tj=25°C



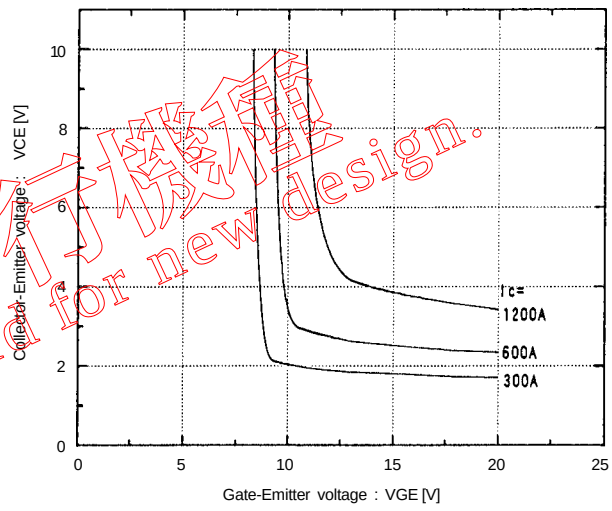
Collector current vs. Collector-Emitter voltage
Tj=125°C



Collector-Emitter vs. Gate-Emitter voltage
Tj=25°C

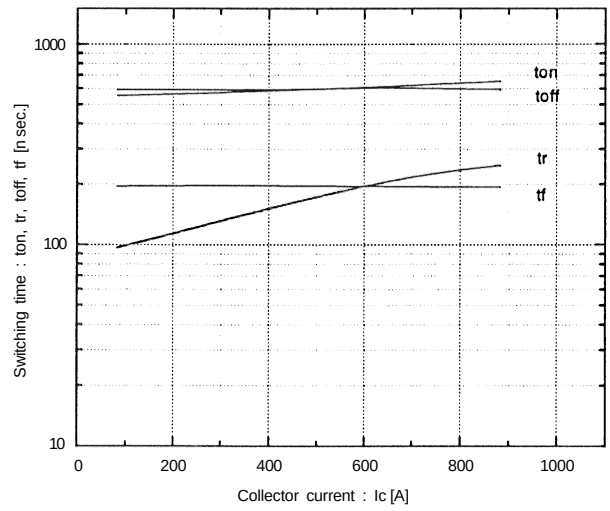


Collector-Emitter vs. Gate-Emitter voltage
Tj=125°C

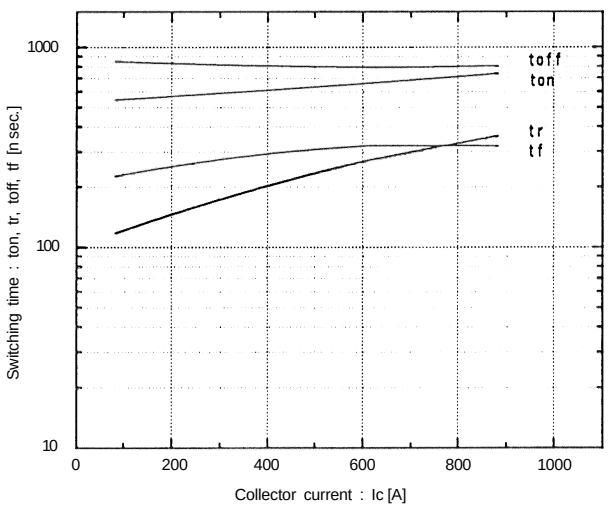


Not recommend for new design.
但不推荐新设计

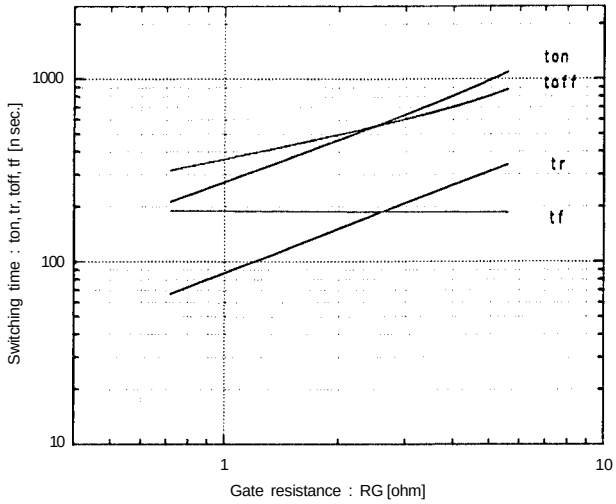
Switching time vs. Collector current
Vcc=300V, RG=2.7 ohm, VGE=±15V, Tj=25°C



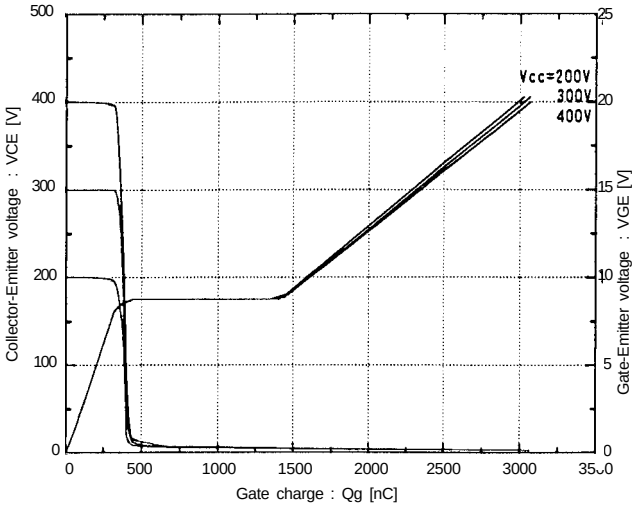
Switching time vs. Collector current
Vcc=300V, RG=2.7 ohm, VGE=±15V, Tj=125°C



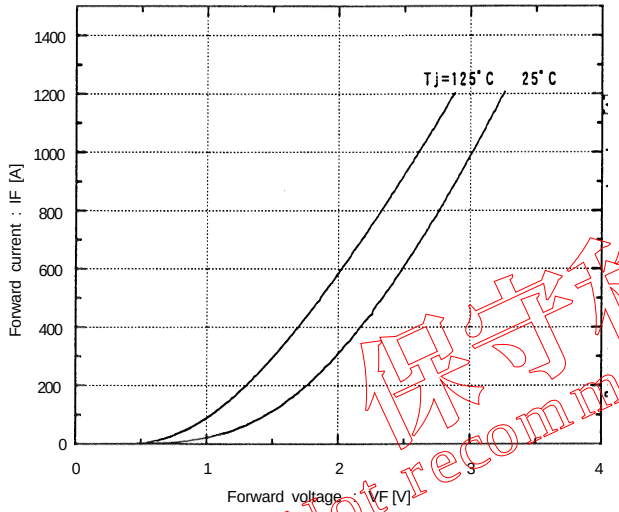
Switching time vs. RG
Vcc=300V, Ic=600A, VGE=±15V, Tj=25°C



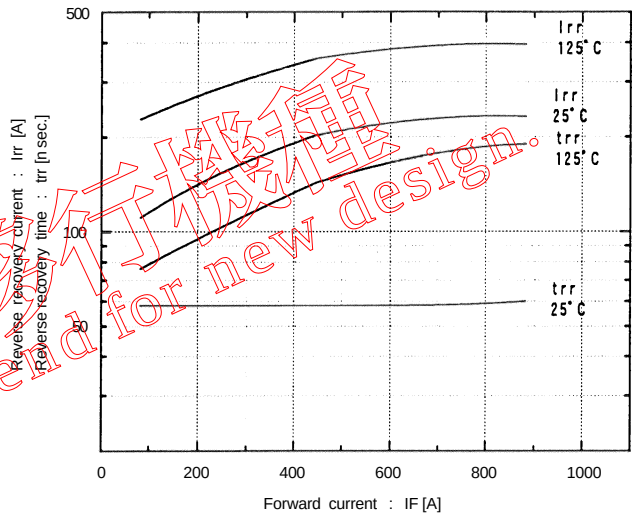
Dynamic input characteristics
Tj=25°C



Forward current vs. Forward voltage
VGE=0V

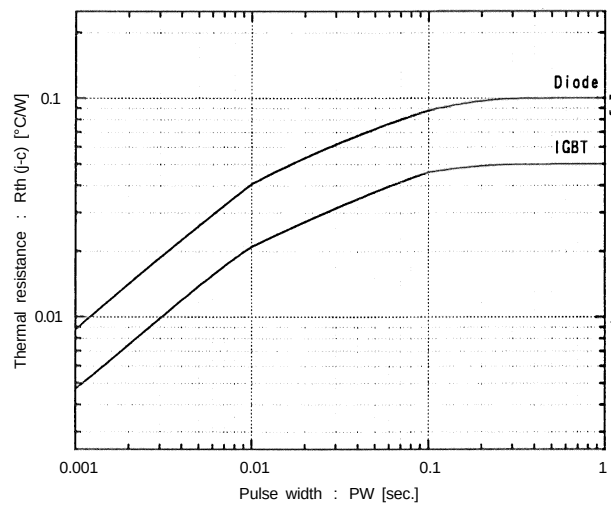


Reverse recovery characteristics
trr, Irr, vs. IF

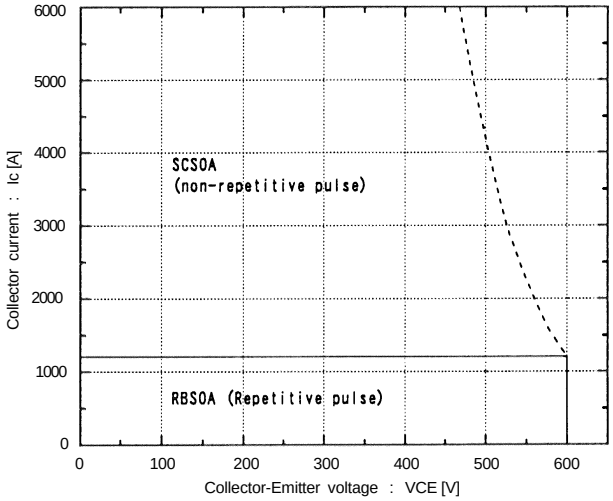


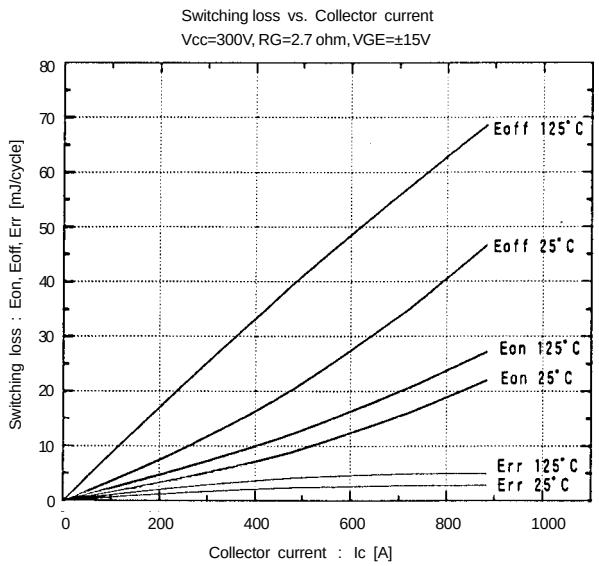
保守推介不建议使用
Not recommend for new design.

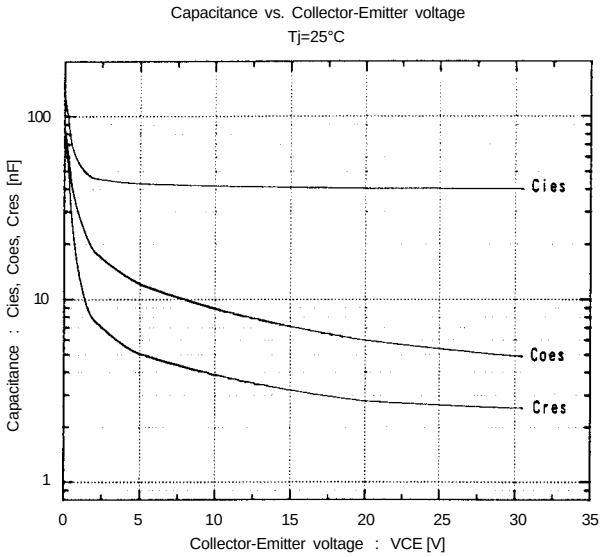
Transient thermal resistance



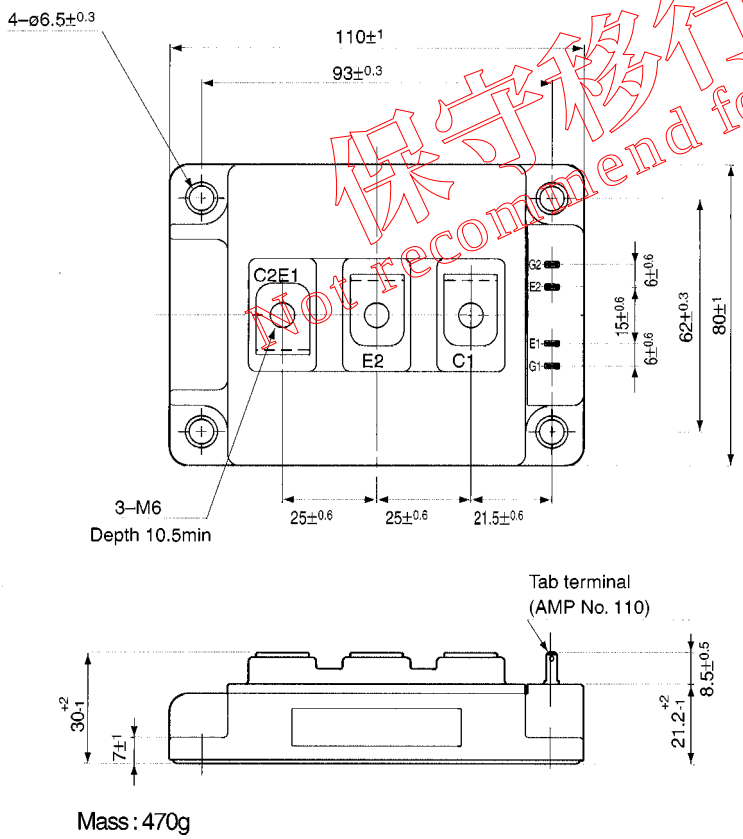
Reversed biased safe operating area
+VGE=15V, -VGE ≦ 15V, Tj ≦ 125°C, RG ≧ 2.7 ohm







■ Outline Drawings, mm



Mass : 470g

保守移行機種
Not recommend for new design.